Product data sheet

1. General description

Silicon Carbide Schottky diode in a DFN 8*8 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- · Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- · Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant

3. Applications

- · Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			6	50		V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; $T_c \le 146$ °C; Fig. 1; Fig. 2; Fig. 3	12			А	
T_j	junction temperature			175		°C	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 12 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.8	2.2	V
Dynamic	characteristics						
Q _r	recovered charge	$I_F = 12 \text{ A}; dI_F/dt = 500 \text{ A/}\mu\text{s}; V_R = 400 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 7$		-	17.5	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	[]	K — A
2	n.c.	not connected	5	001aaa020
3	А	anode		
4	А	anode	0	
5	К	mounting base; connected to cathode	1 2 3 4	

6. Ordering information

Table 3. Ordering information

Туре	number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNS	C2D12650T	DFN8*8	WNSC2D12650TJ	Таре	3000	DFN8X8N	25-Dec-2019

7. Marking

Table 4. Marking codes

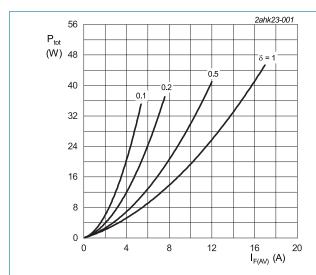
Type number	Marking codes
WNSC2D12650T	WNSC2D 12650T

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V_R	reverse voltage	DC	650	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_c \le 146$ °C; Fig. 1; Fig. 2; Fig. 3	12	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _c ≤ 146 °C; square-wave pulse	24	А
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	60	А
	forward current	t_p = 10 μs; $T_{j(init)}$ = 25 °C; square-wave pulse	600	Α
l ² t	I ² t for fusing	sine-wave pulse; T _{j(init)} = 25 °C; t _p = 10 ms	18	A ² s
T _{stg}	storage temperature		-55 to 175	°C
T _j	junction temperature		175	°C



 $\begin{aligned} &I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta} \\ &V_o = 0.884 \text{ V; } R_s = 0.1054 \text{ }\Omega \end{aligned}$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

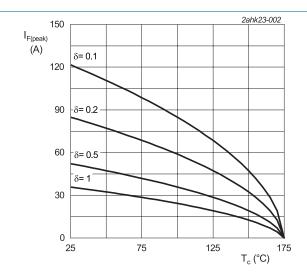
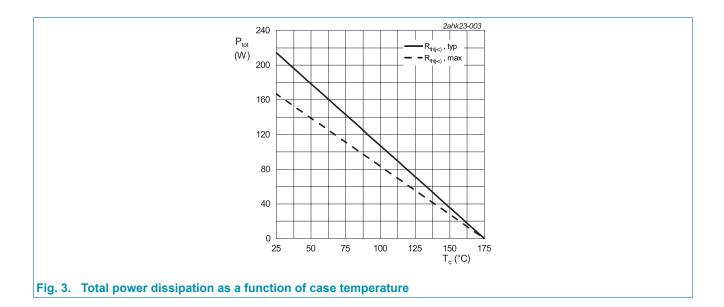


Fig. 2. Current derating as a function of case temperature



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-c)}	thermal resistance from junction to case	Fig. 4	-	0.7	0.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

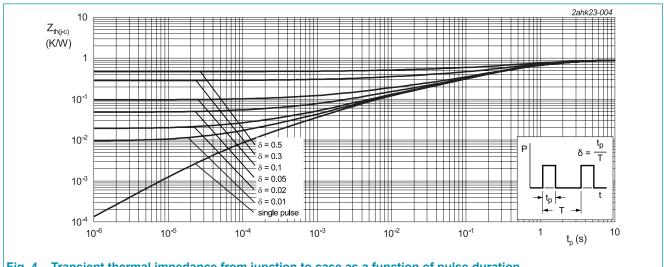
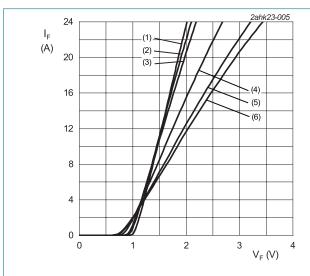


Fig. 4. Transient thermal impedance from junction to case as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward current	I _F = 12 A; T _j = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.8	2.2	V
		I _F = 12 A; T _j = 175 °C; <u>Fig. 5</u>	-	2	2.3	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C; <u>Fig. 6</u>	-	0.6	60	μΑ
		V _R = 650 V; T _j = 175 °C; <u>Fig. 6</u>	-	30	300	μΑ
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 12 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	17.5	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	380	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	44	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C	-	41	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 4.6 A; L = 5 mH; T _{j(init)} = 25 °C	55	-	-	mJ



 $V_o = 0.884 \text{ V}; R_s = 0.1054 \Omega$

(1) T_j = -55 °C; typical values

(2) T_j = 0 °C; typical values

(3) T_i = 25 °C; typical values

(4) $T_i = 100 \,^{\circ}\text{C}$; typical values

(5) $T_j = 150$ °C; typical values

(6) T_i = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

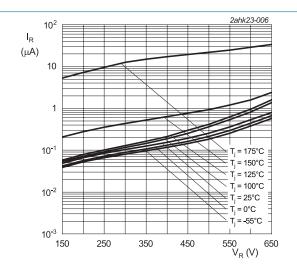
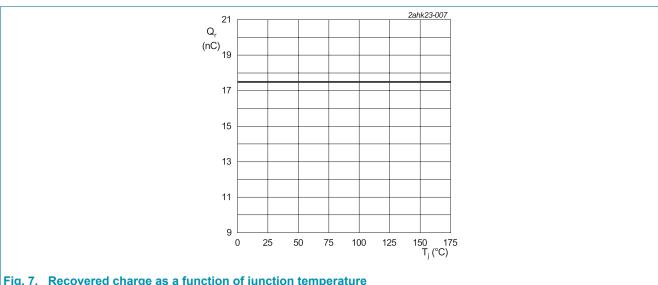
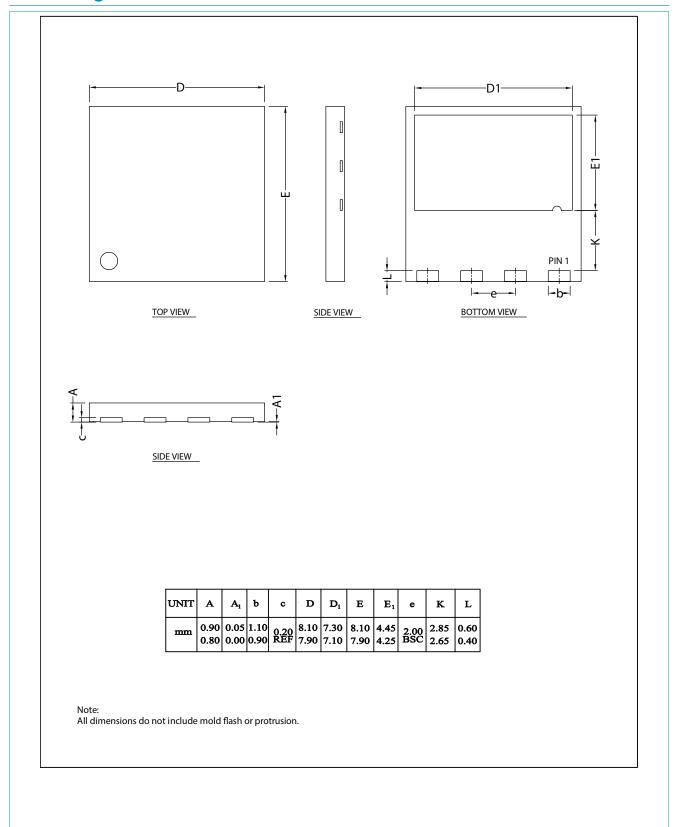


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value



11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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